



**America Semiconductor**

**Silicon Standard  
Recovery Diode**

**1N3671A thru  
1N3673AR**

**V<sub>RRM</sub> = 50 V - 1000 V**

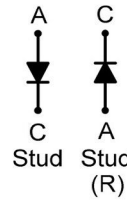
**I<sub>F</sub> = 12 A**

**Features**

- High Surge Capability
- Types up to 1000 V V<sub>RRM</sub>

**Note:**

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



**DO-4 Package**



**Maximum ratings, at T<sub>j</sub> = 25 °C, unless otherwise specified**

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>		800	1000	V
RMS reverse voltage	V <sub>RMS</sub>		560	700	V
DC blocking voltage	V <sub>DC</sub>		800	1000	V
Continuous forward current	I <sub>F</sub>	T <sub>C</sub> ≤ 150 °C	12	12	A
Surge non-repetitive forward current, Half Sine Wave	I <sub>F,SM</sub>	T <sub>C</sub> = 25 °C, t <sub>p</sub> = 8.3 ms	240	240	A
Operating temperature	T <sub>j</sub>		-65 to 200	-65 to 200	°C
Storage temperature	T <sub>stg</sub>		-65 to 200	-65 to 200	°C

**Electrical characteristics, at T<sub>j</sub> = 25 °C, unless otherwise specified**

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> = 12 A, T <sub>j</sub> = 25 °C	1.1	1.1	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 50 V, T <sub>j</sub> = 25 °C	10	10	μA
		V <sub>R</sub> = 50 V, T <sub>j</sub> = 175 °C	15	15	mA

**Thermal characteristics**

Thermal resistance, junction - case	R <sub>thJC</sub>		2.00	2.00	°C/W
-------------------------------------	-------------------	--	------	------	------



